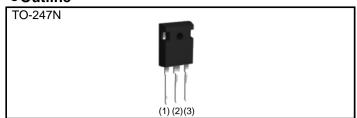


RGS80TSX2DHR

1200V 40A Field Stop Trench IGBT

V _{CES}	1200V
I _{C (100°C)}	40A
V _{CE(sat) (Typ.)}	1.7V
P_D	555W

Outline



Features

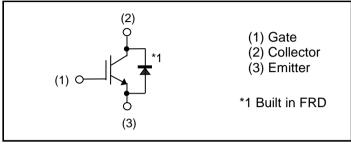
- 1) Low Collector Emitter Saturation Voltage
- 2) Short Circuit Withstand Time 10µs
- 3) Qualified to AEC-Q101
- 4) Built in Very Fast & Soft Recovery FRD
- 5) Pb free Lead Plating; RoHS Compliant

Application

General Inverter

for Automotive and Industrial Use

●Inner Circuit



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Typo	Tape Width (mm)	-
Type	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGS80TSX2D

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	1200	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	80	А
Collector Current	T _C = 100°C	I _C	40	А
Pulsed Collector Current		I _{CP} *1	120	А
Diode Forward Current	T _C = 25°C	I _F	80	А
	T _C = 100°C	I _F	40	А
Diode Pulsed Forward Current		I _{FP} ^{*1}	120	А
Dawer Dissination	T _C = 25°C	P _D	555	W
Power Dissipation	T _C = 100°C	P _D	277	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax}.

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei	Symbol	Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.27	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j-c)}$	-	-	0.56	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions		Unit		
r arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	1200	ı	ı	V
		$V_{CE} = 1200V, V_{GE} = 0V$				
Collector Cut - off Current	I _{CES}	T _j = 25°C	-	-	10	μΑ
		$T_j = 25^{\circ}C$ $T_j = 175^{\circ}C$	-	3	-	mA
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±500	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 6.1mA$	5.0	6.0	7.0	V
		$I_C = 40A, V_{GE} = 15V$				
Collector - Emitter Saturation Voltage	V _{CE(sat)}	T _j = 25°C	-	1.70	2.10	V
		T _j = 175°C	-	2.20	-	V

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter Symbol	Symbol	Conditions		Unit		
	Conditions	Min.	Тур.	Max.	Offic	
Input Capacitance	C _{ies}	V _{CE} = 30V	-	2820	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V$	-	161	ı	pF
Reverse transfer Capacitance	C _{res}	f = 1MHz	-	25	ı	
Total Gate Charge	Q_g	V _{CE} = 500V	-	104	ı	
Gate - Emitter Charge	Q_ge	I _C = 40A	-	25	ı	nC
Gate - Collector Charge	Q_{gc}	$V_{GE} = 15V$	-	42	1	
Turn - on Delay Time	t _{d(on)}		-	49	-	
Rise Time	t _r	$I_C = 40A, V_{CC} = 600V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	27	-	no
Turn - off Delay Time	t _{d(off)}	$T_i = 25^{\circ}C$	-	199	-	ns
Fall Time	t _f	Inductive Load *E _{on} include diode reverse recovery	-	227	-	
Turn-on Switching Loss	E _{on}		-	3.00	-	mJ
Turn-off Switching Loss	E _{off}		-	3.10	-	
Turn - on Delay Time	t _{d(on)}		-	49	-	
Rise Time	t _r	$I_C = 40A, V_{CC} = 600V,$ $V_{GE} = 15V, R_G = 10\Omega,$	-	40	-	no
Turn - off Delay Time	t _{d(off)}	$T_i = 175^{\circ}C$	-	258	-	ns
Fall Time	t _f	Inductive Load	-	371	-	
Turn-on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	3.80	-	
Turn-off Switching Loss	E _{off}		-	4.50	-	mJ
Reverse Bias Safe Operating Area	RBSOA	$I_C = 120A, V_{CC} = 1050V$ $V_p = 1200V, V_{GE} = 15V$ $R_G = 50\Omega, T_j = 175^{\circ}C$	FULL SQUARE		-	
Short Circuit Withstand Time	t _{sc}	$V_{CC} \le 600V$ $V_{GE} = 15V, T_j = 25^{\circ}C$	10	-	-	μs
Short Circuit Withstand Time	t _{sc} *2	$V_{CC} \le 600V$ $V_{GE} = 15V, T_j = 150^{\circ}C$	8	-	-	μs

^{*2} Design assurance without measurement

●FRD Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol		Min.	Тур.	Max.	Offic
		I _F = 40A				
Diode Forward Voltage	V _F	$T_j = 25^{\circ}C$	-	1.65	2.10	V
		T _j = 175°C	-	1.85	-	
Diode Reverse Recovery Time	t _{rr}		-	198	1	ns
Diode Peak Reverse Recovery Current	I _{rr}	$I_F = 40A$ $V_{CC} = 600V$ $di_F/dt = 500A/\mu s$ $T_j = 25^{\circ}C$	-	21.7	-	А
Diode Reverse Recovery Charge	Q _{rr}		-	2.5	ı	μC
Diode Reverse Recovery Energy	E _{rr}		-	568	-	μJ
Diode Reverse Recovery Time	t _{rr}		-	337	-	ns
Diode Peak Reverse Recovery Current	I _{rr}	$I_{F} = 40A$ $V_{CC} = 600V$	-	29.1	1	А
Diode Reverse Recovery Charge	Q _{rr}	di _F /dt = 500A/µs T _j = 175°C	-	5.9	-	μC
Diode Reverse Recovery Energy	E _{rr}		-	1708	-	μJ

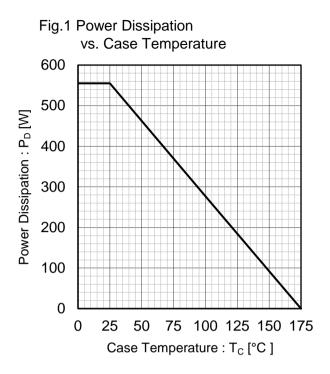


Fig.2 Collector Current vs. Case Temperature 100 80 Collector Current : Ic [A] 60 40 20 T_i ≤ 175°C V_{GE} ≥ 15V 0 25 75 100 125 150 175 0 Case Temperature : T_C [°C]

Fig.3 Forward Bias Safe Operating Area 1000 10µs 100 Collector Current : I_C [A] 100µs 10 1 0.1 T_C = 25°C Single Pulse 0.01 10 100 1000 10000 Collector To Emitter Voltage: V_{CE} [V]

140 120 Collector Current : Ic [A] 100 80 60 40 20 T_i ≤ 175°C _{GE} = 15V 0 0 400 800 1200 1600 Collector To Emitter Voltage : V_{CE} [V]

Fig.4 Reverse Bias Safe Operating Area

Fig.5 Typical Output Characteristics

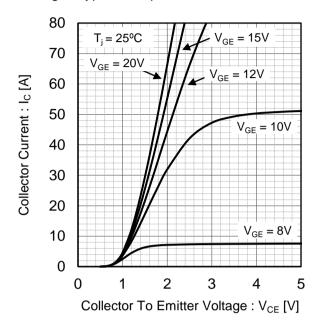


Fig.6 Typical Output Characteristics

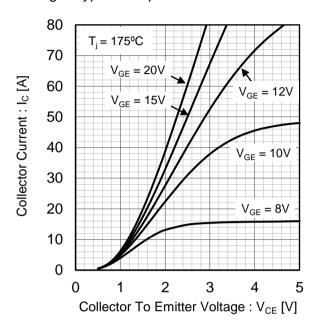


Fig.7 Typical Transfer Characteristics

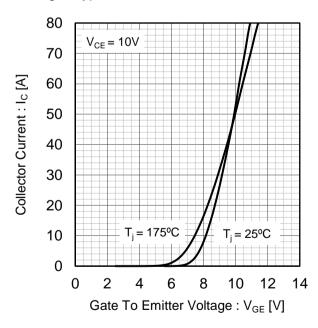
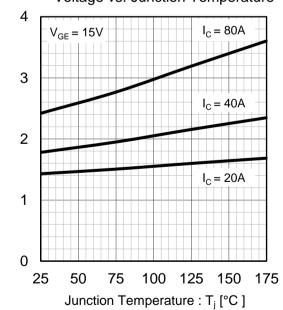


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Collector To Emitter Saturation

Voltage: V_{CE(sat)} [V]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

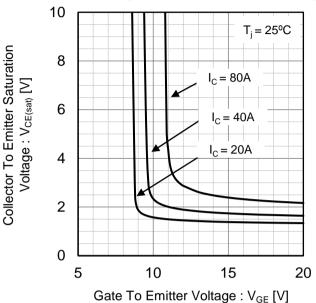


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

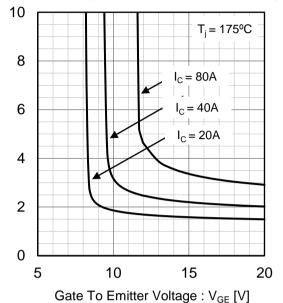


Fig.11 Typical Switching Time vs. Collector Current

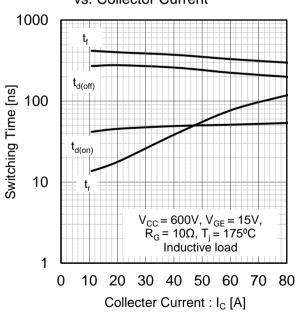
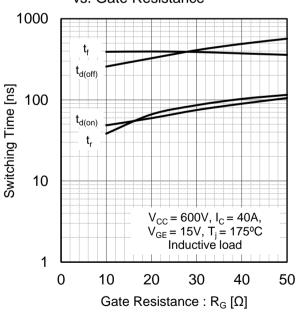


Fig.12 Typical Switching Time vs. Gate Resistance



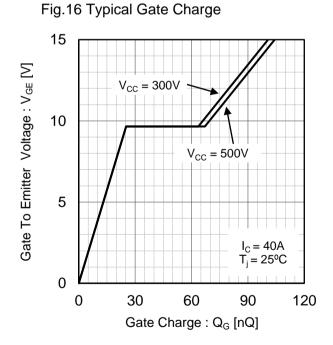
Collector To Emitter Saturation

Voltage: V_{CE(sat)} [V]

Fig.13 Typical Switching Energy Losses vs. Collector Current 100 Switching Energy Losses [mJ] E_{on} 10 $\mathsf{E}_{\mathsf{off}}$ 1 V_{CC} = 600V, V_{GE} = 15V, R_G = 10 Ω , T_j = 175°C Inductive load 0.1 0 10 20 30 40 50 60 70 80 Collector Current : I_C [A]

Fig.14 Typical Switching Energy Losses vs. Gate Resistance 100 Switching Energy Losses [mJ] 10 E_{on} $\mathsf{E}_{\mathsf{off}}$ 1
$$\begin{split} &V_{CC}=600\text{V},\,V_{GE}=15\text{V},\\ &I_{C}=40\text{A},\,T_{j}=175^{o}\text{C}\\ &\text{Inductive load} \end{split}$$
0.1 0 10 20 30 40 50 Gate Resistance : $R_G[\Omega]$

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 C_{ies} 1000 Capacitance [pF] Coes 100 10 f = 1MHz C_{res} $V_{GE} = 0V$ T_i = 25°C 1 100 0.01 0.1 1 10 Collector To Emitter Voltage: V_{CE} [V]



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Fig.17 Typical Diode Forward Current vs. Forward Voltage 80 70 Forward Current : I_F [A] 60 50 40 30 20 $T_{i} = 175^{\circ}C$ 10 = 25°C 0 1.5 0 0.5 2 2.5 3 Forward Voltage: V_F [V]

vs. Forward Current 500 Reverse Recovery Time : t_{rr}[ns] 400 $T_i = 175^{\circ}C$ 300 200 $T_i = 25^{\circ}C$ 100 $V_{CC} = 600V$ di_F/dt = 500A/µs Inductive load 0 0 10 20 30 40 50 60 70 80 Forward Current : I_F [A]

Fig.18 Typical Diode Reverce Recovery Time

Fig.19 Typical Diode Reverse Recovery Current vs. Forward Current 40 35 Reverse Recovery Current : Irr [A] $T_i = 175^{\circ}C$ 30 25 20 15 $T_i = 25^{\circ}C$ 10 $V_{CC} = 600V$ di_F/dt = 500A/µs 5 Inductive load 0 0 10 20 30 40 50 60 70 80 Forward Current : I_F [A]

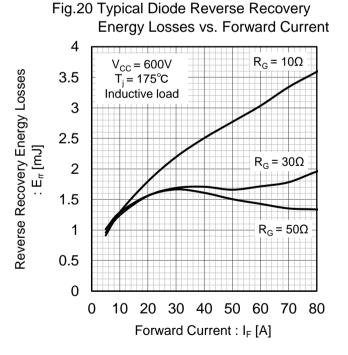


Fig.21 IGBT Transient Thermal Impedance

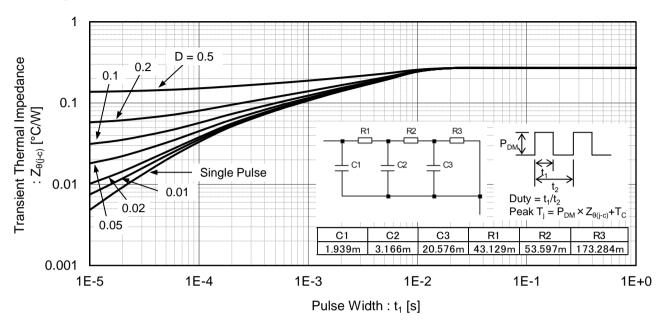
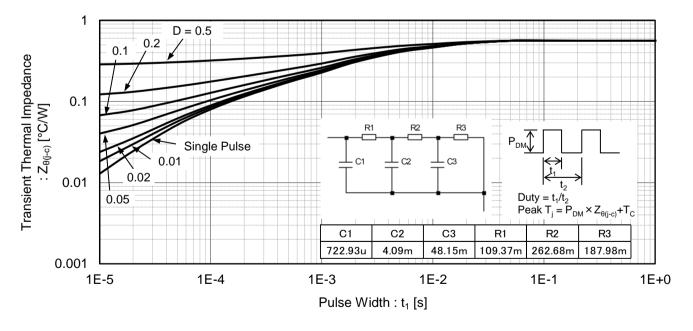


Fig.22 Diode Transient Thermal Impedance



Inductive Load Switching Circuit and Waveform

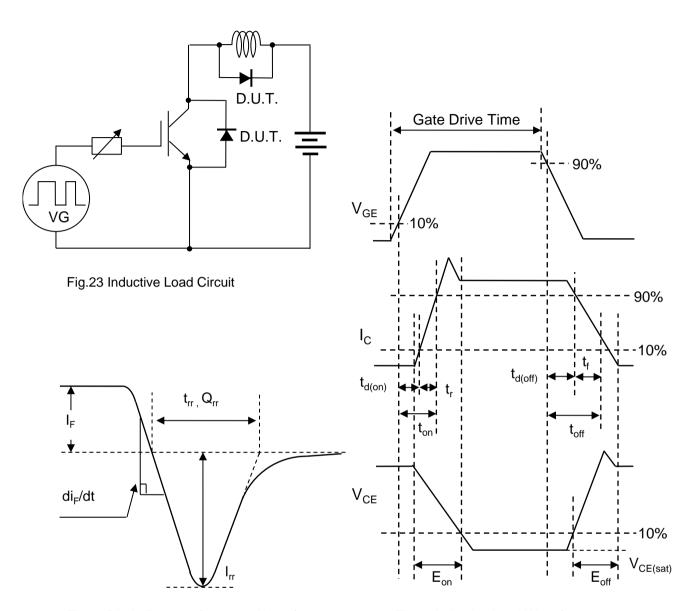


Fig.24 Diode Reverce Recovery Waveform

Fig.25 Inductive Load Waveform

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